

ABSTRACT OF THE DISCLOSURE

Forming of a first silicon oxide film is started on an internal surface of a trench formed on a surface or upwardly of a semiconductor substrate according to an HDP technique. Then, deposition of the first silicon oxide film stops before an opening of the trench closes. Further, the first silicon oxide film deposited in the vicinity of an opening is etched, and a second silicon oxide film is formed on the first silicon oxide film deposited on the bottom of the trench according to the HDP technique. In this manner, the first and second silicon oxide films can be laminated on the bottom of the trench.